

**15 A, 1200 V, Hyperfast Diode**

The RHRP15120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

**Features**

- Hyperfast Recovery  $t_{rr} = 75$  ns (@  $I_F = 15$  A)
- Max Forward Voltage,  $V_F = 3.2$  V (@  $T_C = 25^\circ\text{C}$ )
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

**Applications**

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

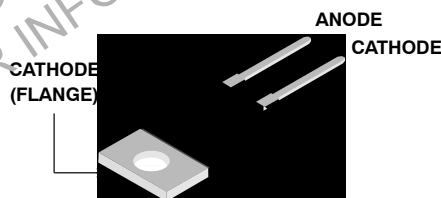
**Ordering Information**

PART NUMBER	PACKAGE	BRAND
RHRP15120	TO-220AC-2L	RHRP15120

NOTE: When ordering, use the entire part number.

**Packaging**

JEDEC TO-220AC

**Symbol****Absolute Maximum Ratings**  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RHRP15120	UNIT
Peak Repetitive Reverse Voltage . . . . .	$V_{RRM}$ 1200	V
Working Peak Reverse Voltage . . . . .	$V_{RWM}$ 1200	V
DC Blocking Voltage . . . . .	$V_R$ 1200	V
Average Rectified Forward Current . . . . . ( $T_C = 140^\circ\text{C}$ )	$I_{F(AV)}$ 15	A
Repetitive Peak Surge Current . . . . . (Square Wave, 20 kHz)	$I_{FRM}$ 30	A
Nonrepetitive Peak Surge Current . . . . . (Halfwave, 1 Phase, 60 Hz)	$I_{FSM}$ 200	A
Maximum Power Dissipation . . . . .	$P_D$ 100	W
Avalanche Energy (See Figures 10 and 11) . . . . .	$E_{AVL}$ 20	mJ
Operating and Storage Temperature . . . . .	$T_{STG}, T_J$ -65 to 175	$^\circ\text{C}$

**Electrical Specifications**  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
$V_F$	$I_F = 15\text{ A}$	--		3.2	V
	$I_F = 15\text{ A}$ , $T_C = 150^\circ\text{C}$	--		2.6	V
$I_R$	$V_R = 1200\text{ V}$	--		100	$\mu\text{A}$
	$V_R = 1200\text{ V}$ , $T_C = 150^\circ\text{C}$	--		500	$\mu\text{A}$
$T_{rr}$	$I_F = 1\text{ A}$ , $dI_F/dt = 100\text{ A}/\mu\text{s}$	--		65	ns
	$I_F = 15\text{ A}$ , $dI_F/dt = 100\text{ A}/\mu\text{s}$	--		75	ns
$t_a$	$I_F = 15\text{ A}$ , $dI_F/dt = 100\text{ A}/\mu\text{s}$	--	36	--	ns
$t_b$	$I_F = 15\text{ A}$ , $dI_F/dt = 100\text{ A}/\mu\text{s}$	--	28	--	ns
$Q_{rr}$	$I_F = 15\text{ A}$ , $dI_F/dt = 100\text{ A}/\mu\text{s}$	--	150	--	nC
$C_J$	$V_R = 10\text{ V}$ , $I_F = 0\text{ A}$	--	55	--	pF
$R_{\theta JC}$		--		1.5	$^\circ\text{C}/\text{W}$

**DEFINITIONS**

$V_F$  = Instantaneous forward voltage (pw = 300  $\mu\text{s}$ , D = 2%).

$I_R$  = Instantaneous reverse current.

$t_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current (See Figure 9).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

$Q_{rr}$  = Reverse recovery charge.

$C_J$  = Junction capacitance.

$R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

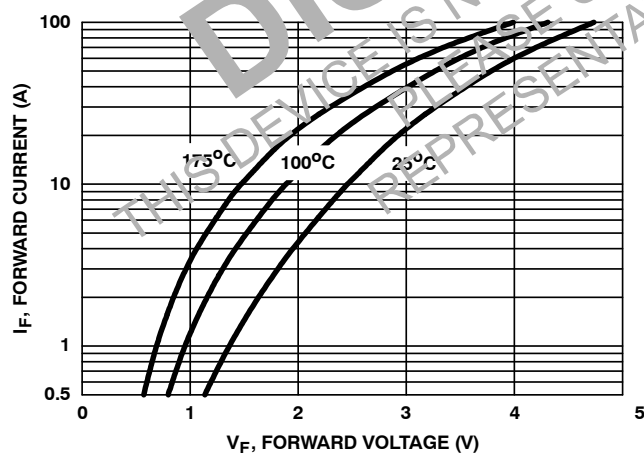
**Typical Performance Curves**

FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

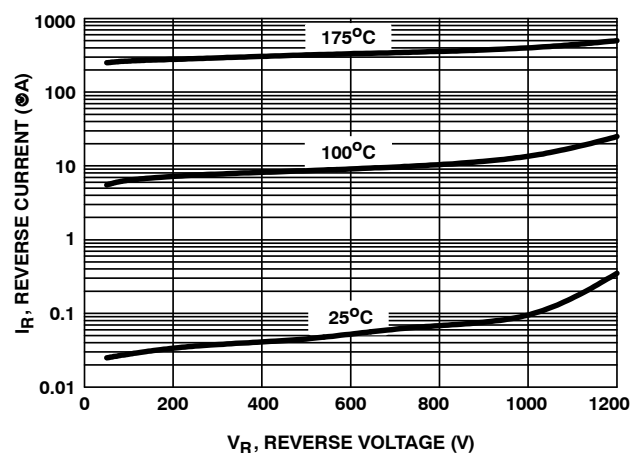


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

## Typical Performance Curves (Continued)

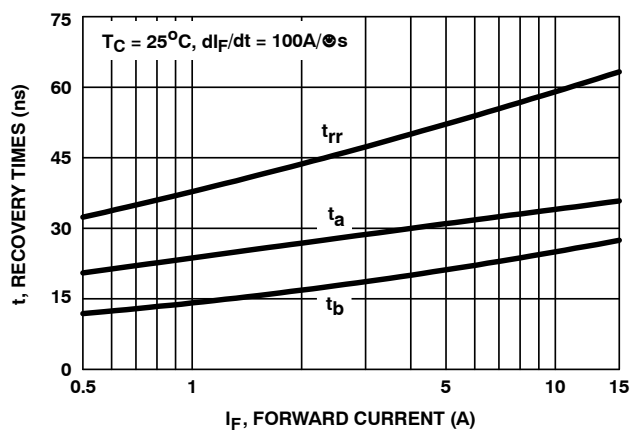
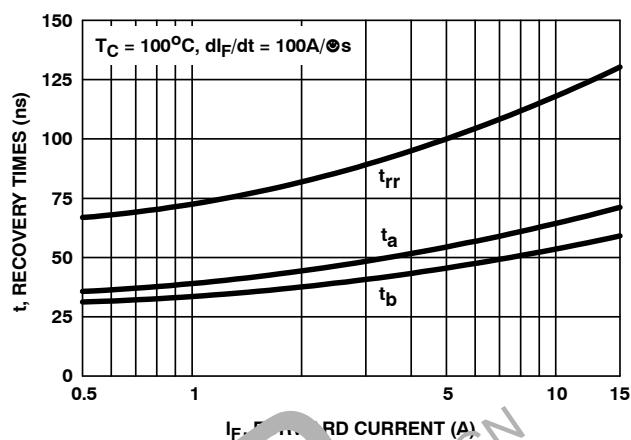
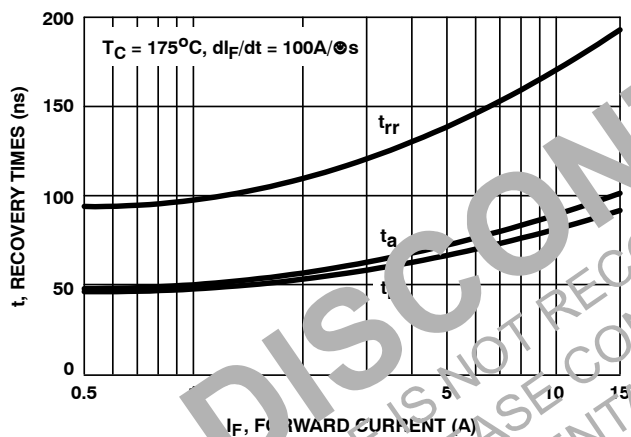
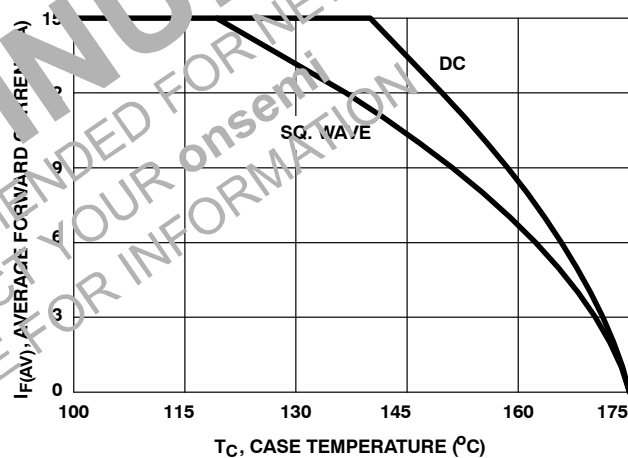
FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENTFIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENTFIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

FIGURE 6. CURRENT DERATING CURVE

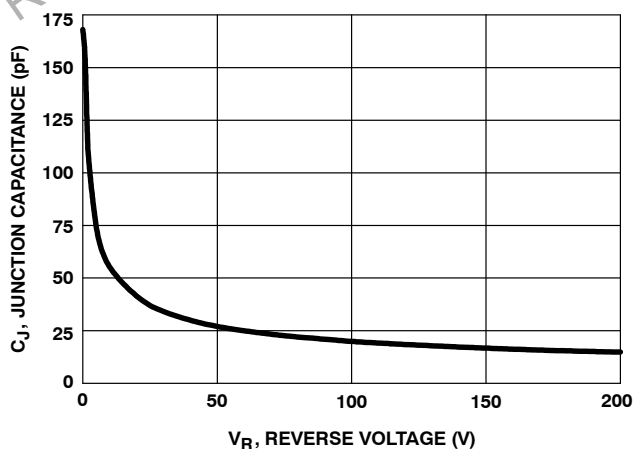


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

## Test Circuits and Waveforms

$V_{GE}$  AMPLITUDE AND  
 $R_G$  CONTROL  $di_F/dt$   
 $t_1$  AND  $t_2$  CONTROL  $I_F$

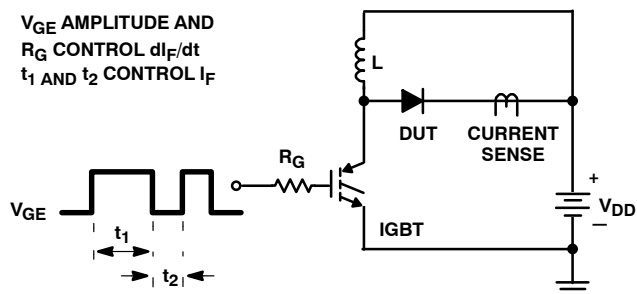


FIGURE 8.  $t_{rr}$  TEST CIRCUIT

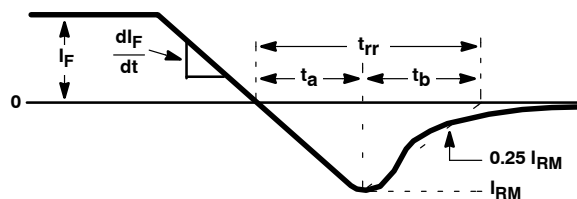


FIGURE 9.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_D)]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

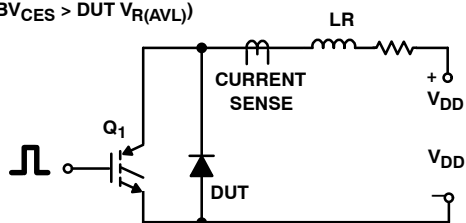



FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT



FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

**DISCONTINUED**  
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
PLEASE CONTACT YOUR onsemi  
REPRESENTATIVE FOR INFORMATION

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent%20Marking.pdf](http://www.onsemi.com/site/pdf/Patent%20Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time and with operating parameters, including "Typical" parameters must be validated by each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303.675.2175 or 800.344.3860 Toll Free USA/Canada  
**Fax:** 303.675.2176 or 800.344.3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800.282.9855 Toll Free  
USA/Canada

**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**Japan Customer Focus Center**  
Phone: 81(3)5817.1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[onsemi:](#)

[RHRP15120](#) [RHRP15120-F102](#)